

**Silicon NPN Power Transistor**

**2SC2518**

**DESCRIPTION**

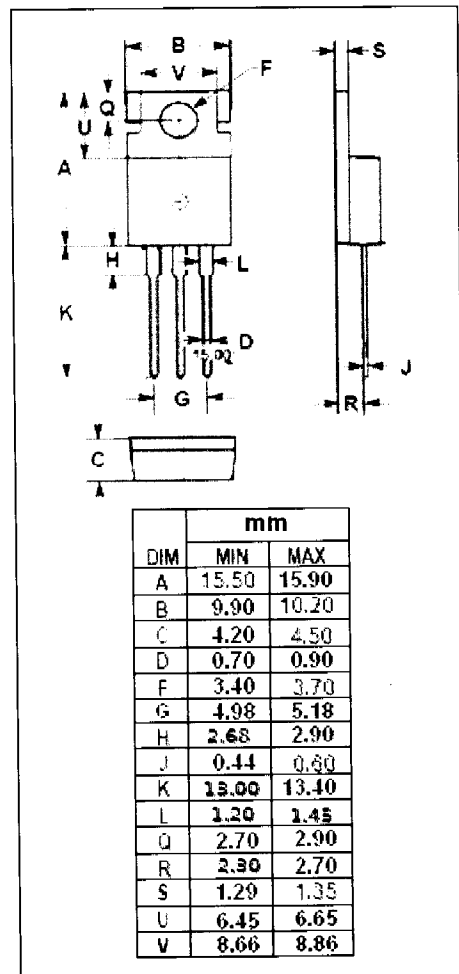
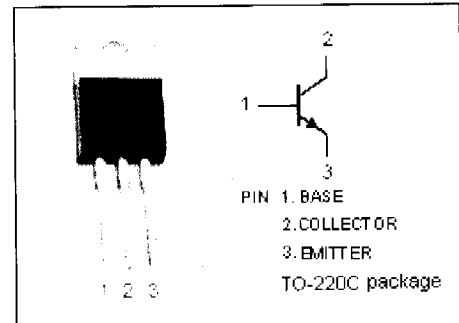
- High Collector-Emitter Sustaining Voltage-  
 $V_{CEO(SUS)} = 400V(\text{Min})$
- Low Collector Saturation Voltage
- High Speed Switching

**APPLICATIONS**

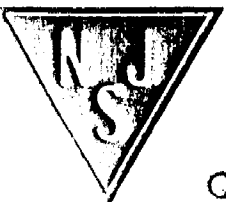
- Designed for switching regulator, DC-DC converter and ultrasonic appliance applications.

**ABSOLUTE MAXIMUM RATINGS ( $T_a = 25^\circ\text{C}$ )**

| SYMBOL    | PARAMETER   | VALUE   | UNIT             |
|-----------|---|---------|------------------|
| $V_{CBO}$ | Collector-Base Voltage                                | 500     | V                |
| $V_{CEO}$ | Collector-Emitter Voltage                             | 400     | V                |
| $V_{EBO}$ | Emitter-Base Voltage                                  | 8       | V                |
| $I_C$     | Collector Current-Continuous                          | 5       | A                |
| $I_{CM}$  | Collector Current-Peak                                | 10      | A                |
| $I_B$     | Base Current-Continuous                               | 2.5     | A                |
| $P_C$     | Total Power Dissipation<br>@ $T_C = 25^\circ\text{C}$ | 40      | W                |
| $T_J$     | Junction Temperature                                  | 150     | $^\circ\text{C}$ |
| $T_{stg}$ | Storage Temperature Range                             | -55~150 | $^\circ\text{C}$ |



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## ELECTRICAL CHARACTERISTICS

$T_C=25^\circ\text{C}$  unless otherwise specified

| SYMBOL         | PARAMETER                            | CONDITIONS  | MIN | MAX       | UNIT                |
|----------------|--------------------------------------|---|-----|-----------|---------------------|
| $V_{CEO(SUS)}$ | Collector-Emitter Sustaining Voltage | $I_C=50\text{mA}; I_B=0$  | 400 |           | V                   |
| $V_{CE(sat)}$  | Collector-Emitter Saturation Voltage | $I_C=2\text{A}; I_B=0.4\text{A}$  |     | 1.0       | V                   |
| $V_{BE(sat)}$  | Base-Emitter Saturation Voltage      | $I_C=2\text{A}; I_B=0.4\text{A}$  |     | 1.5       | V                   |
| $I_{CBO}$      | Collector Cutoff Current             | $V_{CB}=400\text{V}; I_E=0$   |     | 10        | $\mu\text{A}$       |
| $I_{CER}$      | Collector Cutoff Current             | $V_{CE}=400\text{V}; R_{BE}=51\Omega; T_a=125^\circ\text{C}$  |     | 1.0       | mA                  |
| $I_{CEX}$      | Collector Cutoff Current             | $V_{CE}=400\text{V}; V_{BE(off)}=-1.5\text{V}$<br>$V_{CE}=400\text{V}; V_{BE(off)}=-1.5\text{V}; T_a=125^\circ\text{C}$ |     | 10<br>1.0 | $\mu\text{A}$<br>mA |
| $I_{EBO}$      | Emitter Cutoff Current               | $V_{EB}=5\text{V}; I_C=0$   |     | 10        | $\mu\text{A}$       |
| $h_{FE-1}$     | DC Current Gain                      | $I_C=0.5\text{A}; V_{CE}=5\text{V}$   | 20  | 80        |                     |
| $h_{FE-2}$     | DC Current Gain                      | $I_C=2\text{A}; V_{CE}=5\text{V}$   | 10  |           |                     |

### Switching times

|           |              |  |  |     |               |
|-----------|--------------|--|--|-----|---------------|
| $t_{on}$  | Turn-on Time | $I_C=2\text{A}; R_L=75\Omega$<br>$I_{B1}=-I_{B2}=0.4\text{A}; V_{CC}\approx 150\text{V}$ |  | 1.0 | $\mu\text{s}$ |
| $t_{stg}$ | Storage Time |  |  | 2.5 | $\mu\text{s}$ |
| $t_f$     | Fall Time    |  |  | 0.7 | $\mu\text{s}$ |

### ◆ $h_{FE-2}$ Classifications

| M     | L     | K     |
|-------|-------|-------|
| 20-40 | 30-60 | 40-80 |